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		Applicant(s) Fareed et al.	
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*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
	"Molecular Beam Epitaxy of Nitride Thin Films," M. J. Paisley et al., Journal of Crystal Growth, Vol. 127, February 2, 1993, pp. 136-142.
	"Elastic Strain Relaxation and Piezoeffect in GaN-AlN, GaN-AlGaIn and GaN-InGaIn Superlattices," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 81, No. 9, May 1, 1997, pp. 6332-6338.
	"Pulsed Atomic Layer Epitaxy of Quaternary AlInGaIn Layers for Ultraviolet Light Emitters, J. P. Zhang et al., Physica Status Solidi(a), Vol. 188, No. 1, 2001, pp. 95-99.
	"High Optical Quality AlInGaIn by Metalorganic Chemical Vapor Deposition," M. E. Aumer et al., Applied Physics Letters, Vol. 75, No. 21, November 22, 1999, pp. 3315-3317.
	"Low Temperature Growth of Gallium Nitride," H. Gotoh et al., Japanese Journal of Applied Physics, Vol. 20, No. 7, July 1981, pp. L545-L548.
	"Energy Band/Lattice Mismatch Engineering in Quaternary AlInGaIn/GaN Heterostructure," M. A. Khan et al., Physica Status Solidi(a), Vol. 176, No. 1, 1999, pp. 227-230.
	"Strain Energy Bank Engineering Approach to AlN/GaN/InN Heterojunction Devices," A. Khan et al., Frontiers in Electronics: Future Chips Proceedings of the 2002 Workshop on Frontiers in Electronics (WOFE-02) St. Croix, Virgin Islands, World Scientific Publishing Co. (January 15, 2003), pp. 195-214 (1-19).
EXAMINER	DATE CONSIDERED

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